

Lab 4

Part 1: Sizing Chart

ADT Sizing Assistant

Settings Help

LUT Settings

LUTs Directory: ser01/projects/ADT/ex_LUTs/

LUT: pch

Corner: tt

Temp (°C): 27.0

State1 Save State

ID: 10u

Vstar: 200m

L: 1u

VDS: VGS

VSB: 0

Stack: 1

Get Apply

Y-Expr

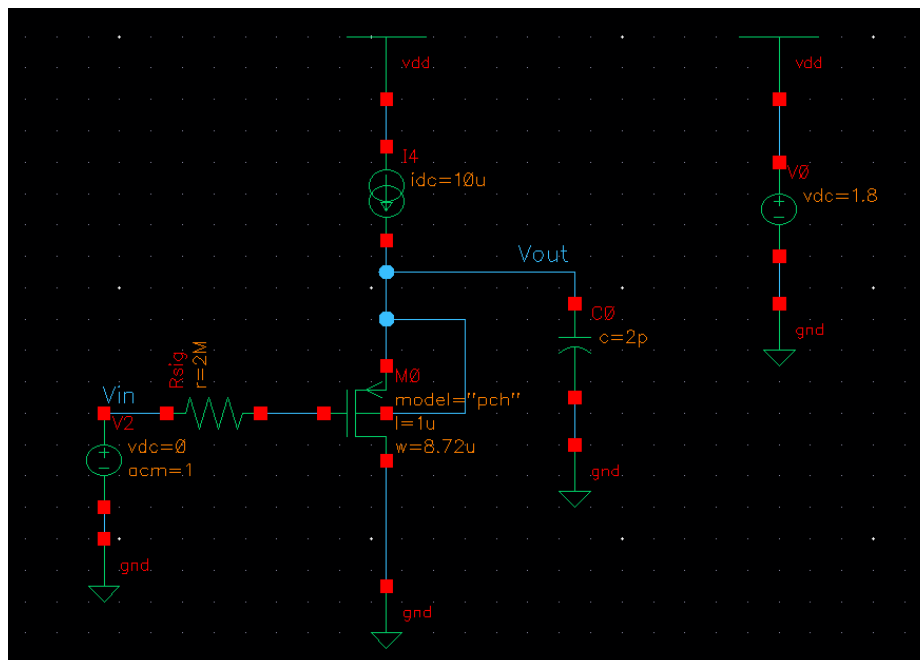
Plot Replace Append

Device Parameters

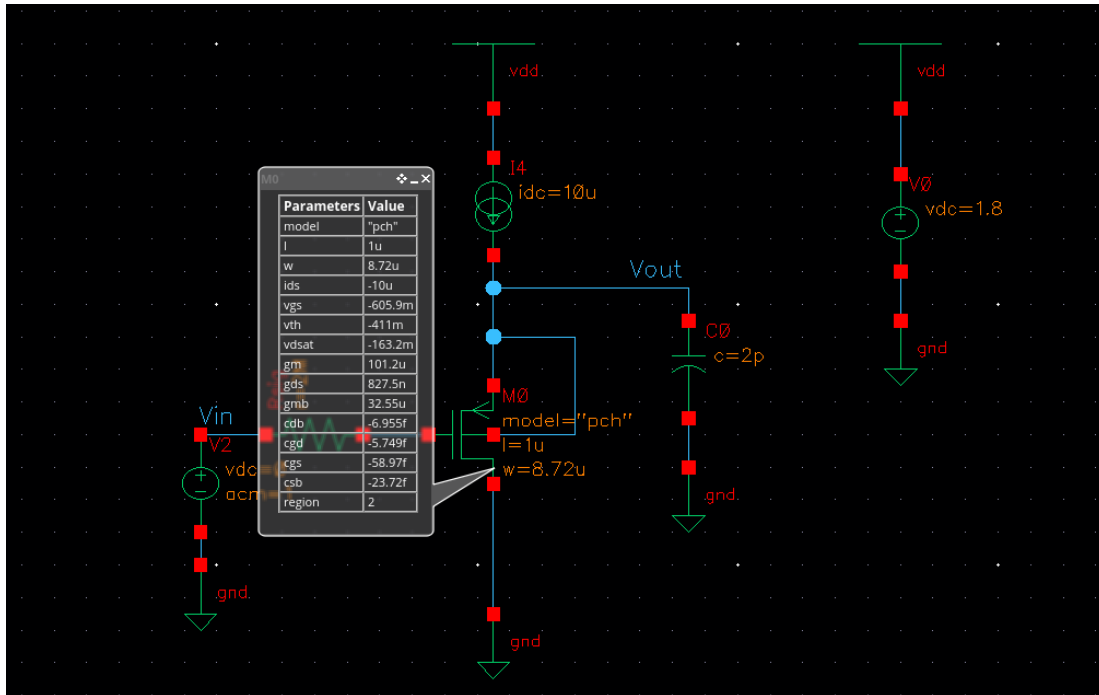
#	Parameter	Value
1	ID	10u
2	L	1u
3	W	8.72u
4	VGS	609.2m
5	VDS	609.2m
6	VSB	0

Part 2: CD Amplifier

Schematic



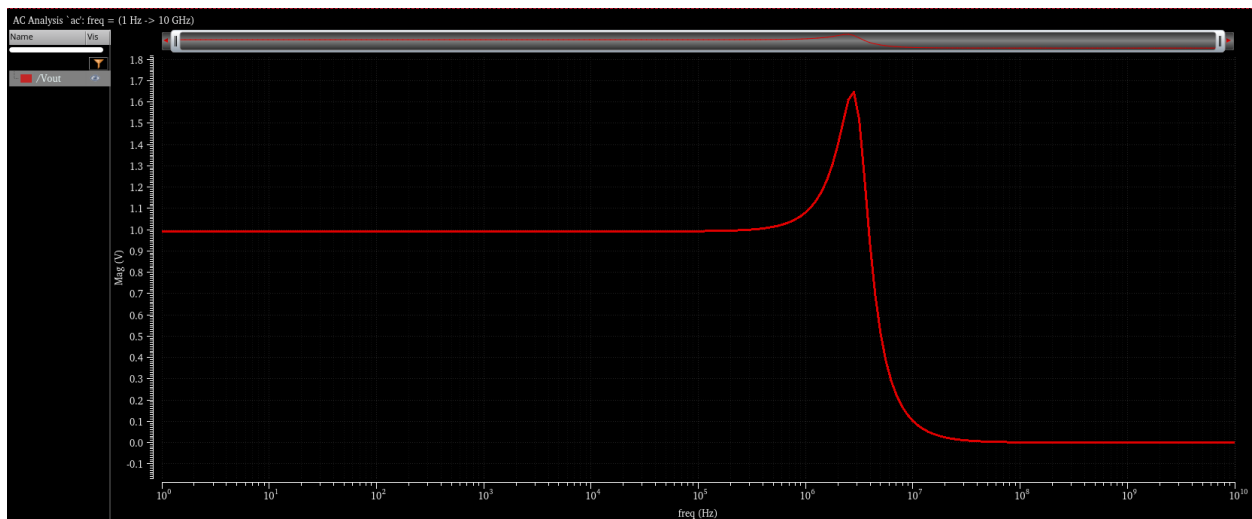
DC OP



Comment: The transistor operates in saturation.

AC Analysis

Bode Plot



Type	Details	Value
expr	<code>ymax(dB20(VF("/Vout")))</code>	4.329

Peaking in frequency domain

Quality Factor Analytic Calculation

Approximate: $Q \approx \sqrt{\frac{gm(C_{gs}+C_{gd})R_{sig}}{c_L}} = \sqrt{\frac{(101.2\mu)(5.75f+59f)(2M)}{2p}} = 2.56 \rightarrow \text{Underdamped system}$

Exact:

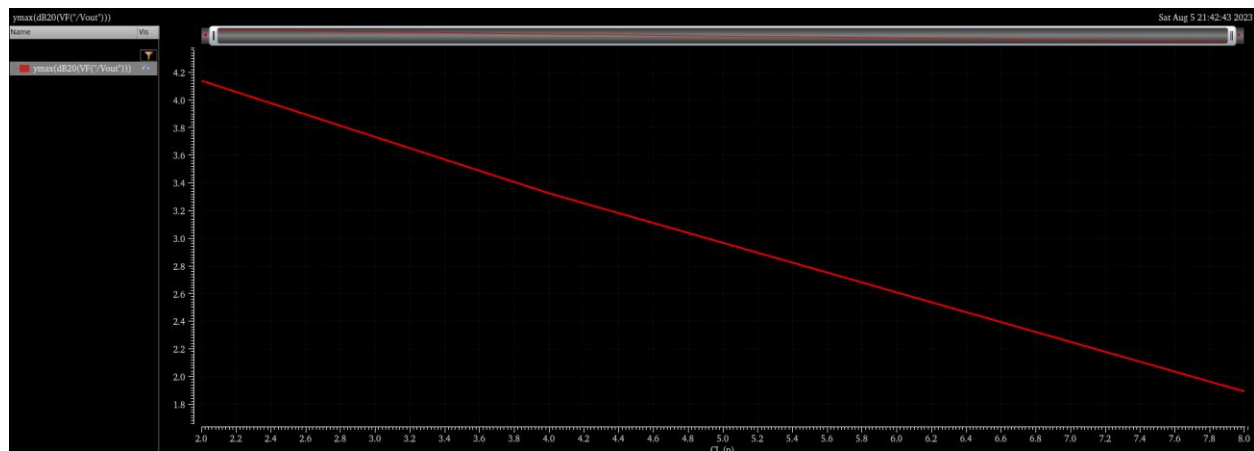
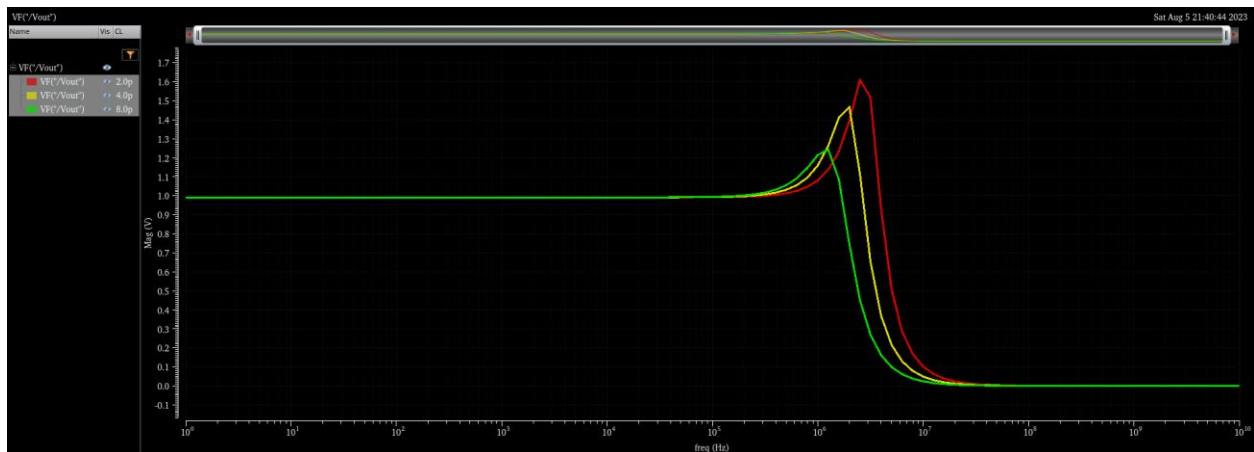
$$b_1 = C_{gd}R_{sig} + \frac{C_{gs} + C_L}{g_m}$$

$$b_2 = \left(\frac{(C_{gs} + C_{gd})C_L + C_{gs}C_{gd}}{g_m} \right) R_{sig}$$

$$\omega_z = \frac{g_m}{C_{gs}}, \omega_o = \frac{1}{\sqrt{b_2}}, Q = \frac{\sqrt{b_2}}{b_1}$$

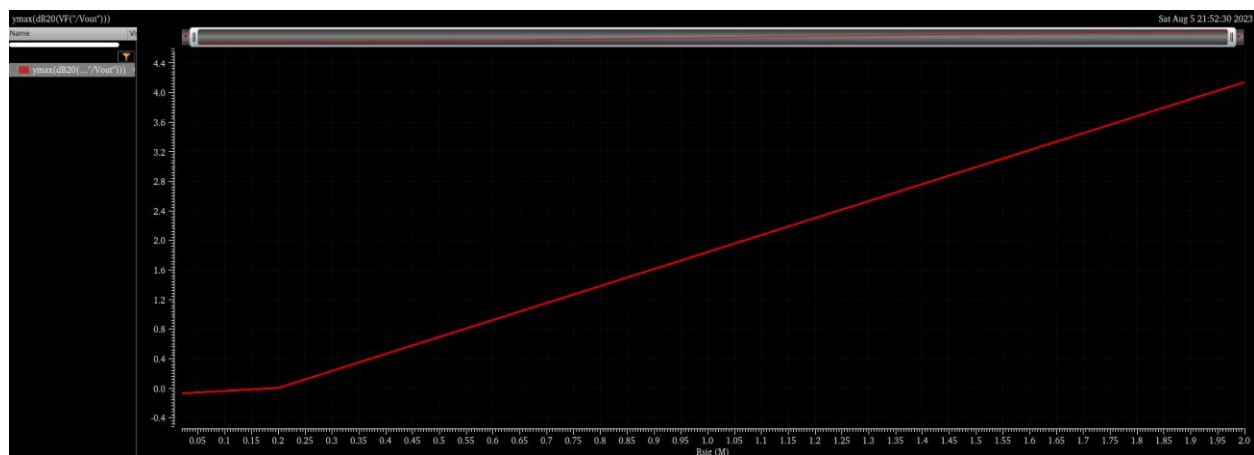
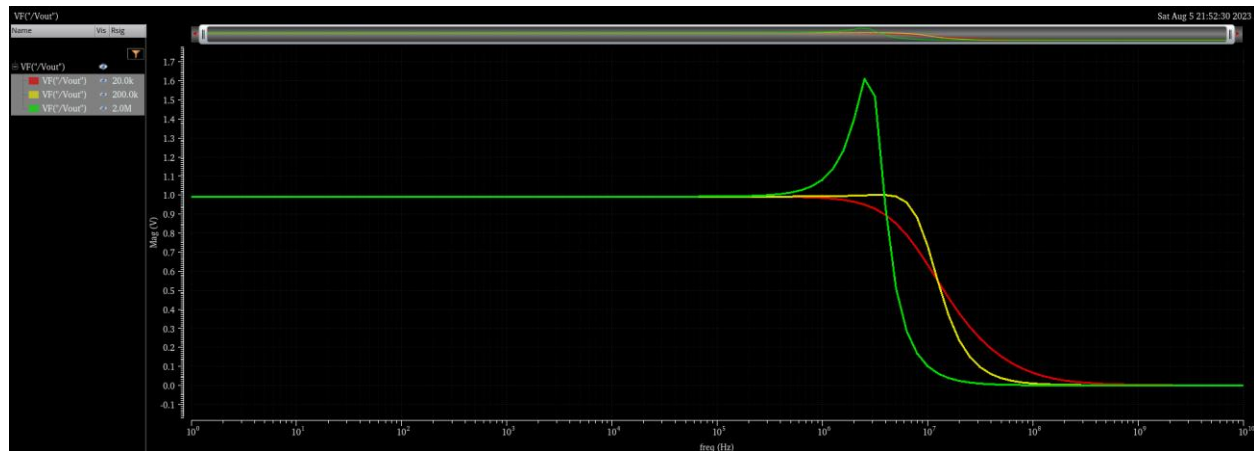
$Q = 1.59 \rightarrow \text{Underdamped system}$

C_L Parametric Sweep



Comment: As C_L increases, the peaking in frequency domain decreases. Increasing C_L eventually decreases $Q \rightarrow \omega_{p,out}$ becomes dominant.

Rsig Parametric Sweep



Comment: As R_{sig} increases, the peaking in frequency domain increases and Q increases.

Transient Analysis



- DC shift = VGS = 605.9 mV
- Using NMOS would shift it downwards.

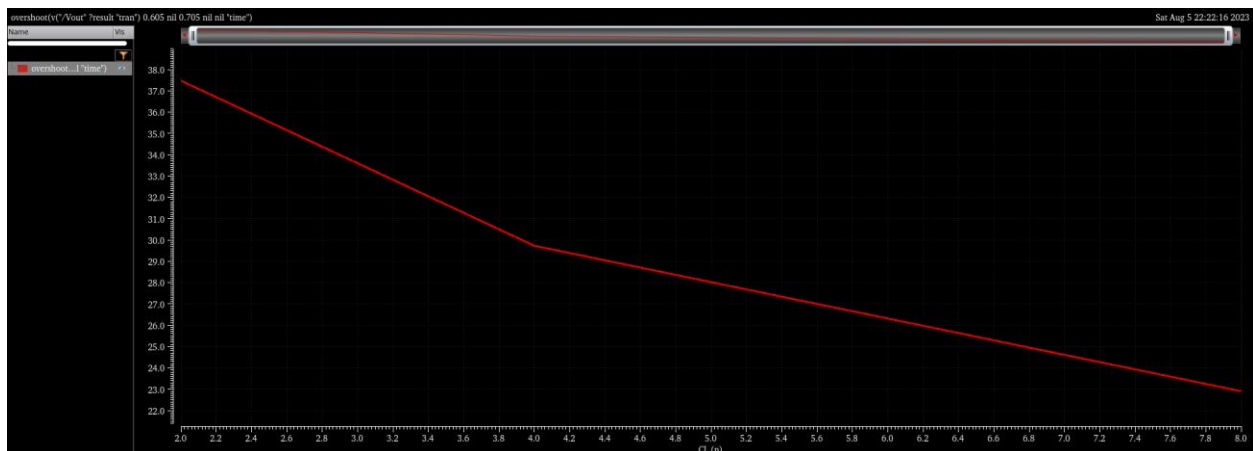
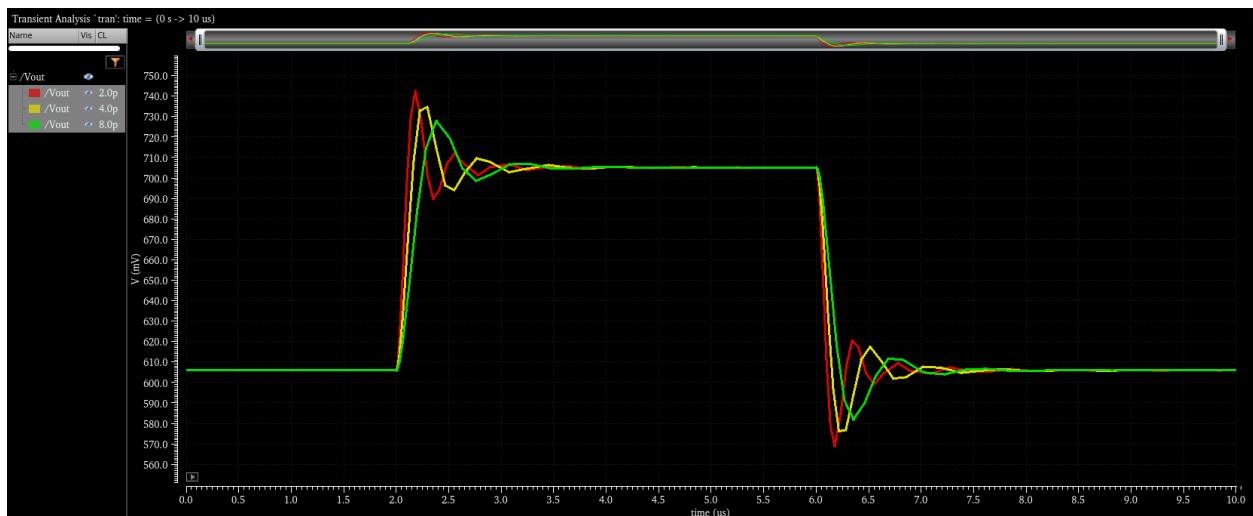
Time Domain Ringing

There is ringing in time domain.

```
overshoot(v("/Vout" ?result "tran" ?resultsDir "/home/user01/simulation/Lab4/part1/maestro/results/maestro/ExplorerRun.0/1/Lab4_part1_1/psf") 605m nil 705m nil nil "time")
```

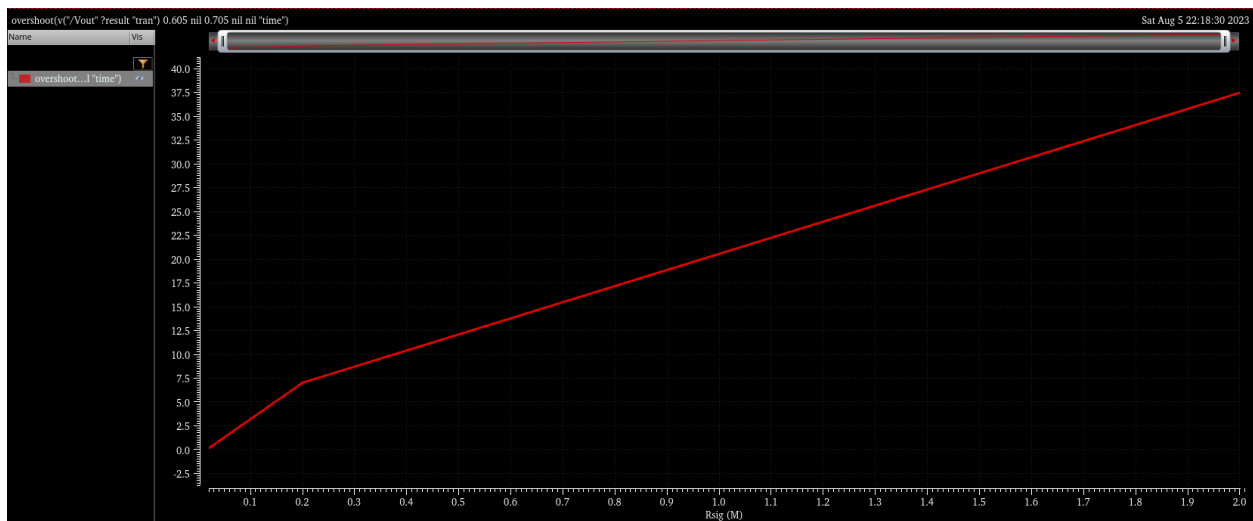
Expression		Value
1	overshoot(v("/Vout" ?result "tran" ?r...	37.48

C_L Parametric Sweep



Comment: As CL increases, the ringing (overshoot) in time domain decreases.

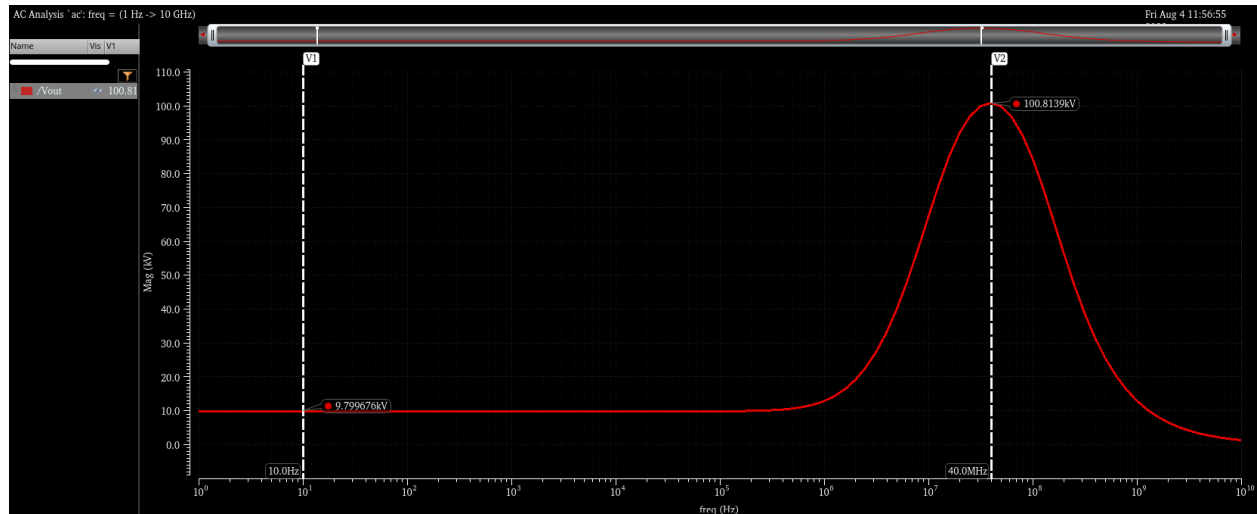
R_{sig} Parametric Sweep



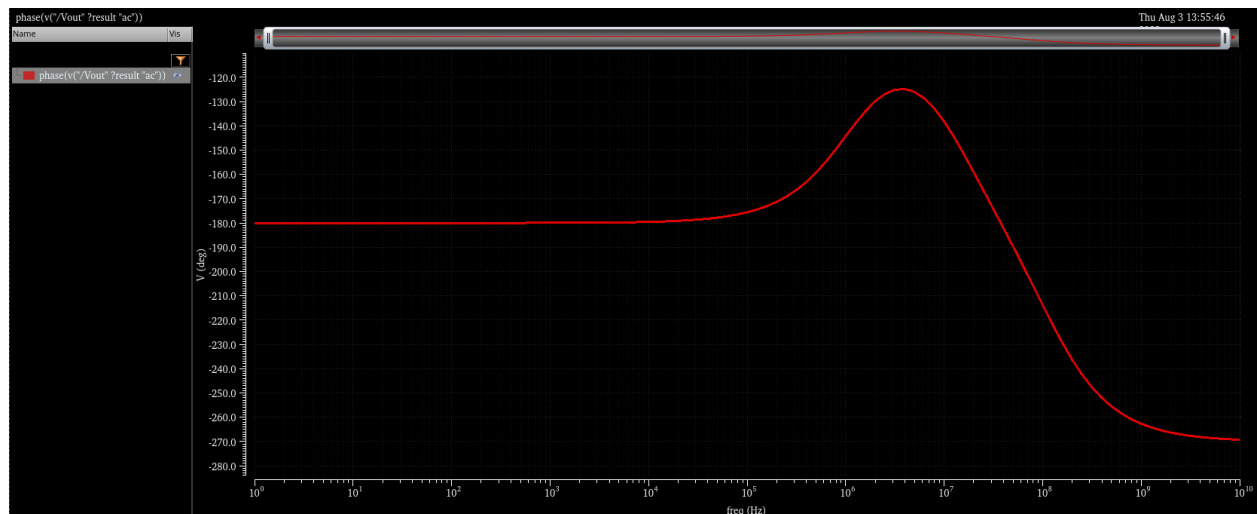
Comment: As R_{sig} increases, the ringing (overshoot) in time domain increases.

Z_{out} (Inductive Rise)

Magnitude



Phase



Comments

- $\omega_z = \frac{1}{R_{sig} C_{gs}}$ & $\omega_p = \frac{gm}{C_{gs}}$
- There is an inductive rise because $R_{sig} (2M) > 1/gm (9.88k)$, so $\omega_z < \omega_p$. This zero causes this inductive rise.

- At high frequency, C_{gd} shunts R_{sig} ($\frac{R_{sig}}{1+sR_{sig}C_{gd}}$). This causes a new pole at this frequency, so we notice that Z_{out} falls.

Analytical Calculations

/poles /zeros				
	qfactor	/poles (Hz)	qfactor	/zeros (Hz)
1	500.0E-3	13.48E6	500.0E-3	1.174E6
2	500.0E-3	115.9E6		

Poles & Zeros

- $f_z = \frac{1}{2\pi R_{sig} C_{gs}} = \frac{1}{2\pi(2M)(59f)} = 1.35 \text{ MHz}$
- $f_{p1} = \frac{1}{2\pi R_{sig} C_{gd}} = \frac{1}{2\pi(2M)(5.75f)} = 13.8 \text{ MHz}$
- $f_{p2} = \frac{g_m}{2\pi C_{gs}} = \frac{101.2\mu}{2\pi(59f)} = 273 \text{ MHz}$ (ro negelected)
- $f_{p2} = \frac{g_m + g_{ds}}{2\pi [R_{sig}.g_{ds}.C_{gs} + C_{gs}]} = 103.7 \text{ MHz}$ (ro taken into account)

Magnitude

- At low frequency, $Z_{out} = \frac{1}{g_m} \left(\frac{1+sR_{sig}C_{gs}}{1+s\frac{C_{gs}}{g_m}} \right)$.
- At higher frequencies, replace R_{sig} with $(R_{sig} || C_{gd})$.
- Let low frequency = 10 Hz \rightarrow Magnitude at $f_L = 9.88k$
- Let high frequency = 40 MHz \rightarrow Magnitude at $f_H = 75.3k$

Comparison

	Simulation	Analytic Calculations
fz	1.17 MHz	1.35 MHz
fp1	13.48 MHz	13.8 MHz
fp2	115.9 MHz	103.7 MHz
Zout_{fL}	9.80k	9.88k
Zout_{fH}	100.8k	75.3k